Structuring or removal of the epoxy based, photo sensitive polymer SU-8 by inductively coupled plasma reactive ion etching (ICP-RIE) was investigated as a function of plasma chemistry, bias power, temperature, and pressure. In a pure oxygen plasma, surface accumulation of antimony from the photo-initiator introduced severe roughness and reduced etch rate significantly. Addition of SF6 to the plasma chemistry reduced the antimony surface concentration with lower roughness and higher etch rate as an outcome. Furthermore the etch anisotropy could be tuned by controlling the bias power. Etch rates up to 800 nm min-1 could be achieved with low roughness and high anisotropy. © 2013 The Authors. Published by Elsevier B.V. All rights reserved.